



ATTORNEY DOCKET 728-203 DIV

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Louis L. HSU, et al. Examiner: not yet known

Serial No.: 10/666,972 Group Art Unit: Not yet assigned

Filed: September 19, 2003 Date: December 18, 2003

For: **MEMORY SYSTEM CAPABLE OF OPERATING AT HIGH
TEMPERATURES AND METHOD FOR FABRICATING THE
SAME**

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

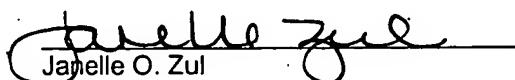
Pursuant to Applicant(s) duty of disclosure, the information listed on the attached form PTO-1449 is brought to the attention of the Examiner. A copy of the non-U.S. Patent publications are enclosed.

The citation of the listed items are not a representation that they constitute a complete or exhaustive listing of the relevant art or that the references are prior art. The items listed are submitted in good faith, but are not intended to be a substitute for the Examiner's search. It is hoped, however, that in addition to apprising the Examiner of these particular items, they will assist in identifying fields of search and in making as full and complete a search as possible.

CERTIFICATION UNDER 37 C.F.R. § 1.8(a)

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Date: December 18, 2003


Janelle O. Zul

The filing of this information disclosure statement is not an admission that the information cited herein is, or is considered to be, material to patentability as defined in 37 C.F.R. § 1.56(b).

- This information disclosure statement is being filed within three (3) months of the filing date of this application.
- This information disclosure statement is being filed within three (3) months of the date of entry of the national stage as set forth in 37 C.F.R. § 1.491 in an international application.
- To the best of Applicant(s) knowledge, this information disclosure statement is being filed before the date of mailing of a first Office Action on the merits in connection with this case.
- Enclosed herewith is a certificate under 37 C.F.R. § 1.97(e)(1).
- Enclosed herewith is a petition under 37 C.F.R. § 1.97(d)(ii).
- Enclosed by check is the petition fee of \$130.00. 37 C.F.R. § 1.17(i)(1))
- Please charge the **\$130.00** petition fee to Deposit Account No. **50-0510/IBM(Yorktown Heights)**.
- Enclosed by check is the **\$180.00** fee required by 37 C.F.R. § 1.17(p).
- Please charge the **\$180.00** fee required by 37 C.F.R. § 1.17(p) to Deposit Account No. **50-0510/IBM(Yorktown Heights)**.

[X] Please charge any deficiency as well as any other fee(s) which may become due under 37 C.F.R. § 1.16 and/or 1.17 at any time during the pendency of this application, or credit any overpayment of such fee(s) to Deposit Account **50-0510/IBM(Yorktown Heights)**. Also, in the event any extensions of time for responding are required for the pending application(s), please treat this paper as a petition to extend the time as required and charge Deposit Account No. **50-0510/IBM(Yorktown Heights)** therefor. **TWO (2) COPIES OF THIS SHEET ARE ENCLOSED.**

Early and favorable consideration of the case is respectfully requested.

Respectfully submitted,



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U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use several sheets if necessary)	ATTY. DOCKET NO. 728-203 DIV	SERIAL NO. 10/666,972
	APPLICANTS Louis L. HSU, et al.	
	FILING DATE September 19, 2003	GROUP ART UNIT not yet known

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		5,539,217	07/23/1996	Edmond et al.			
		5,742,076	04/21/1998	Sridevan et al.			
		5,925,895	07/20/1999	Sriram et al.			

FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES NO

OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)						
			Nemati et al, "A Novel High Density, Low Voltage SRAM Cell with a Vertical NDR Device", on VLSI Technology Digest of Technical Papers, IEEE, pages 66-67, 1998.			
			Nemati et al, "A Novel Thyristor-based SRAM Cell (T-RAM) for High Speed, Low-Voltage, Gig Memories", IEDM 1999, 283-286			

EXAMINER	DATE CONSIDERED

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.